



ACE140P45B

P-Channel Enhancement Mode Power MOSFET

Description

ACE140P45B uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

Features

- $V_{DS} = -40V$, $I_D = -45A$
- $R_{DS(ON)}$ @ $V_{GS} = -10V$, $I_{DS} = -15A$, TYP= 15m Ω
- $R_{DS(ON)}$ @ $V_{GS} = -4.5V$, $I_{DS} = -10A$, TYP= 22m Ω

Absolute Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise noted

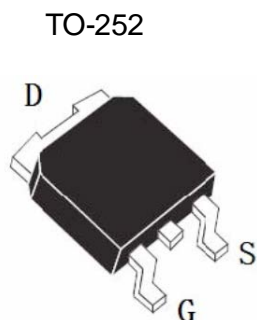
Parameter	Symbol	Max	Unit
Drain-Source Voltage	V_{DSS}	-40	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current (Continuous)*AC	I_D	$T_C = 25^\circ C$	-45
		$T_C = 100^\circ C$	-28
Drain Current (Pulsed)*B	I_{DM}	-60	A
Power Dissipation	P_D	62.5	W
Single Pulse Avalanche Energy	E_{AS}	80	mJ
Thermal Resistance, Junction-to-Case*A	$R_{\theta JC}$	2.4	$^\circ C/W$
Operating temperature / Storage temperature	T_J/T_{STG}	-55~150	$^\circ C$

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the $t \leq 10s$ junction to ambient thermal resistance rating.

Packaging Type



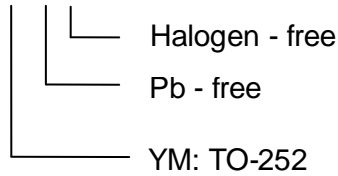


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Ordering information

ACE140P45B XX + H



Electrical Characteristics T_A=25°C, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	-40			V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=-40V, V_{GS}=0V$			-1	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_{DS}=-250\mu A$	-1.2	-1.6	-2.5	V
Gate leakage current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	μA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-12A$		15	20	m Ω
		$V_{GS}=-4.5V, I_D=-8A$		22	28	
Forward Trans conductance	g_{FS}	$V_{DS}=-10V, I_D=-3A$		13		S
Diode forward voltage	V_{SD}	$I_{SD}=-1A, V_{GS}=0V$			-1	V
Diode Forward Current	I_S				-45	A
Switching						
Total Gate Charge	Q_g	$V_{GS}=-4.5V, V_{DS}=-20V, I_D=-12A$		7.9		nC
Gate-Source Charge	Q_{gs}			7.6		
Gate-Drain Charge	Q_{gd}			6.2		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, R_L=1.6\Omega, V_{GS}=-10V, R_{GEN}=3\Omega$		10		ns
Turn-on Rise Time	t_r			18		
Turn-off Delay Time	$t_{d(off)}$			38		
Turn-off Fall Time	t_f			24		
Dynamic						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=-20V, f=1.0MHz$		1870		pF
Output Capacitance	C_{oss}			185		
Reverse Transfer Capacitance	C_{rss}			155		



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Typical Performance Characteristics

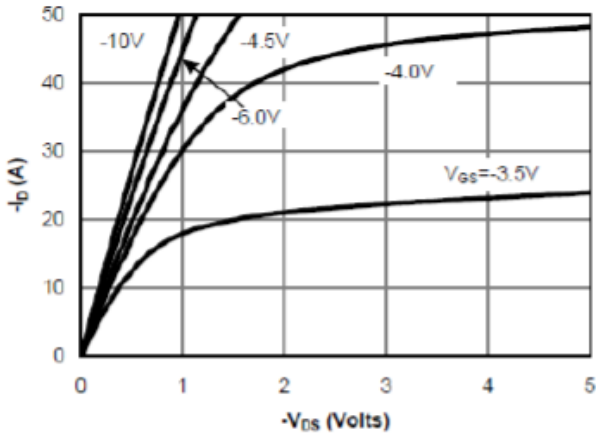


Figure 1: On-Region Characteristics

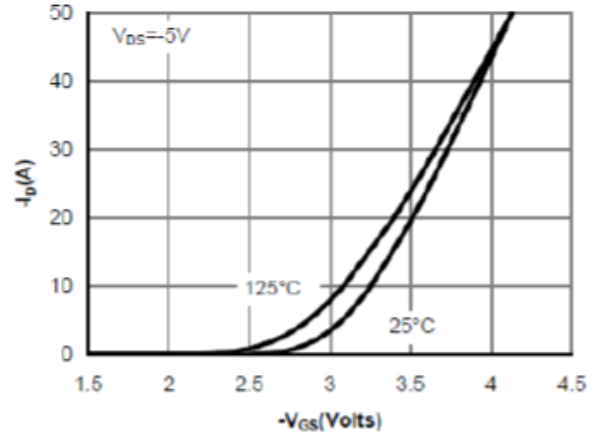


Figure 2: Transfer Characteristics

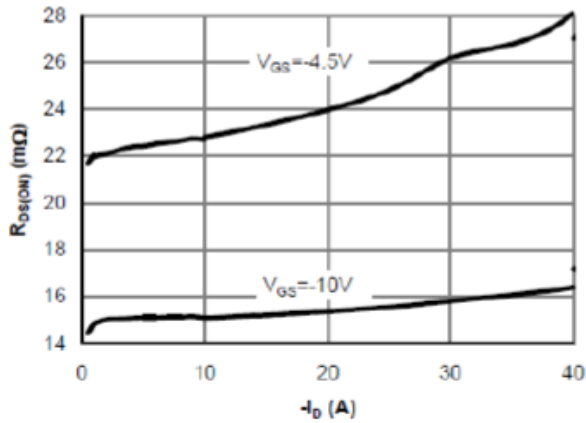


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

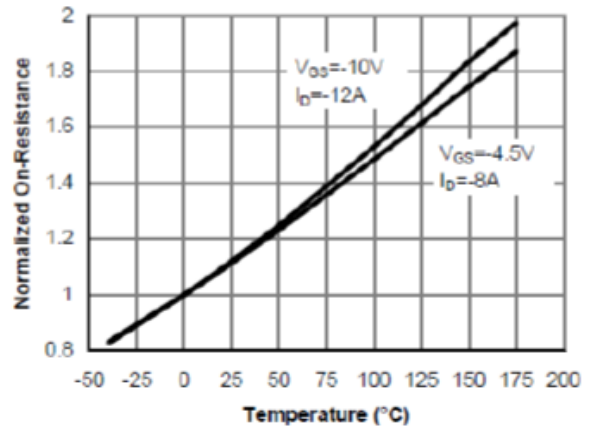


Figure 4: On-Resistance vs. Junction Temperature

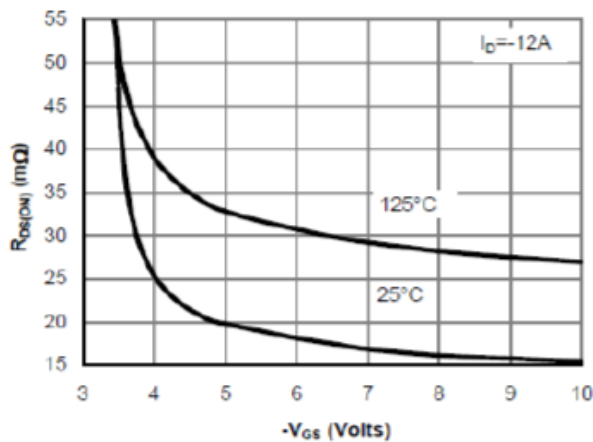


Figure 5: On-Resistance vs. Gate-Source Voltage

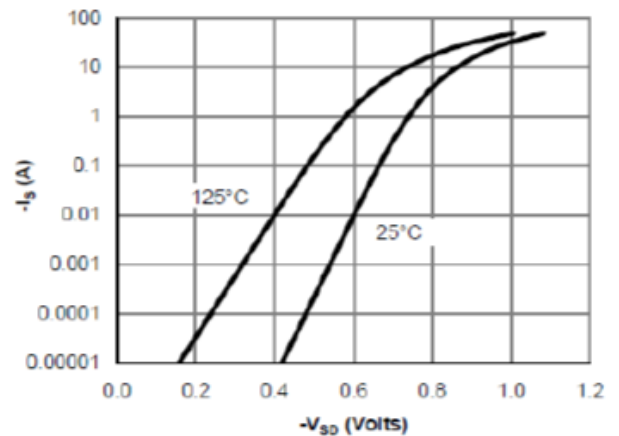


Figure 6: Body-Diode Characteristics



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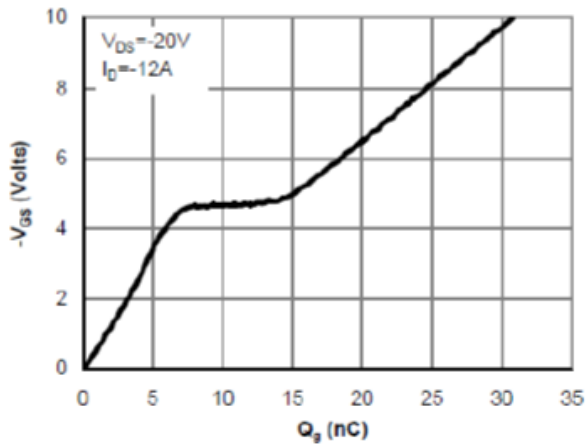


Figure 7: Gate-Charge Characteristics

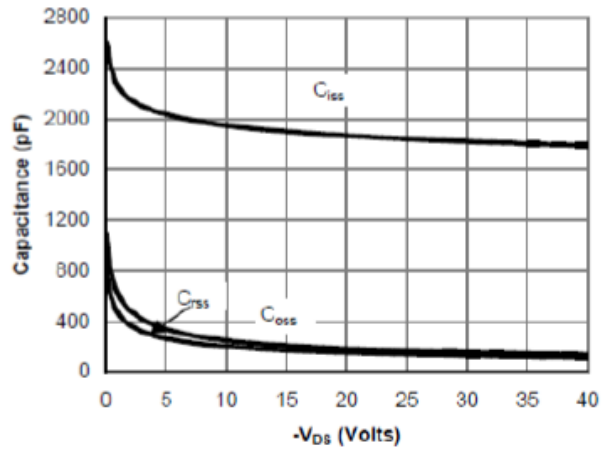


Figure 8: Capacitance Characteristics

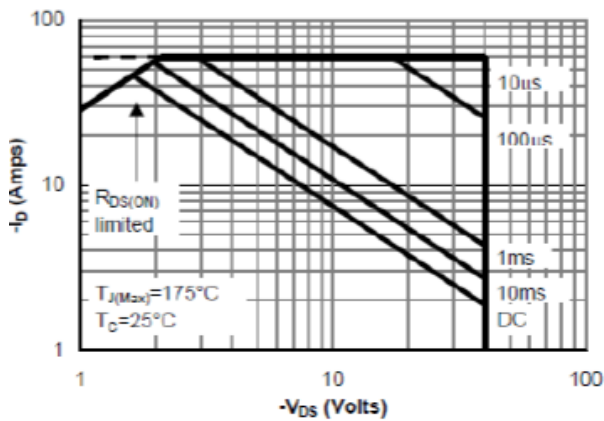


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

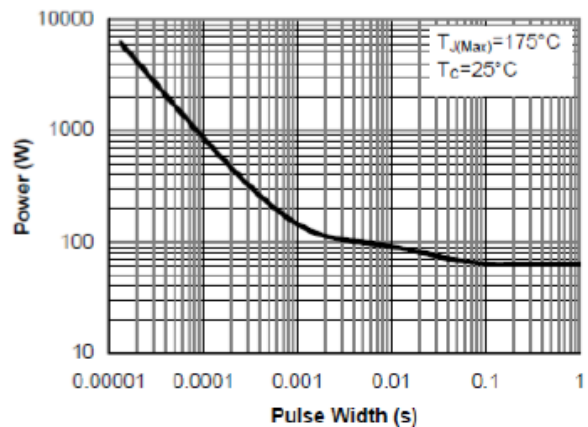


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

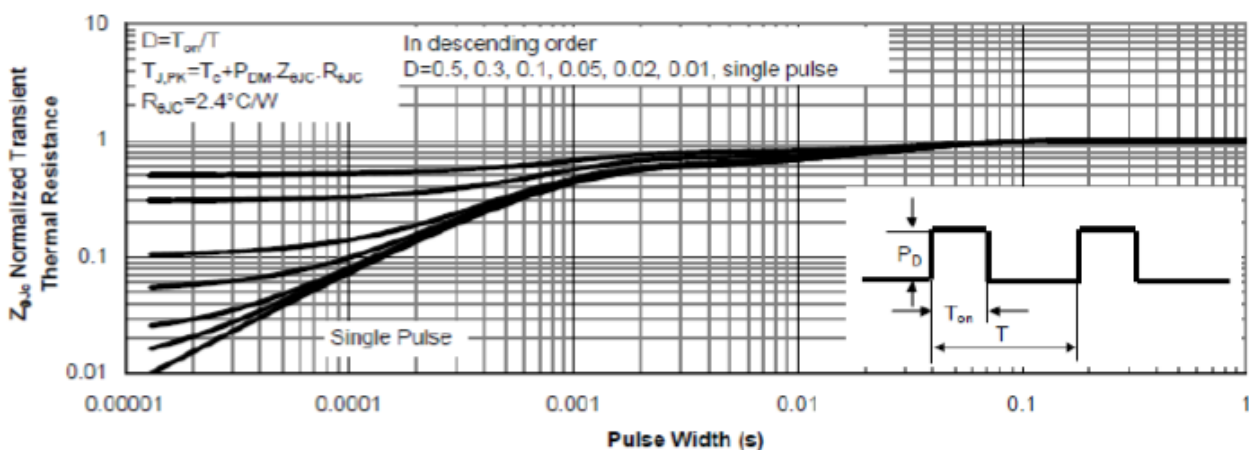


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)



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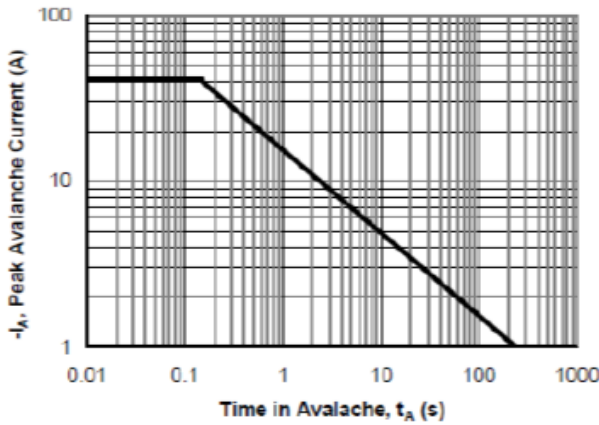


Figure 12: Single Pulse Avalanche Capability

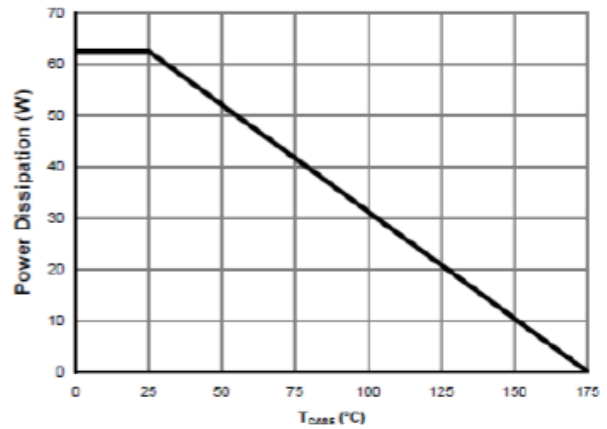


Figure 13: Power De-rating (Note B)

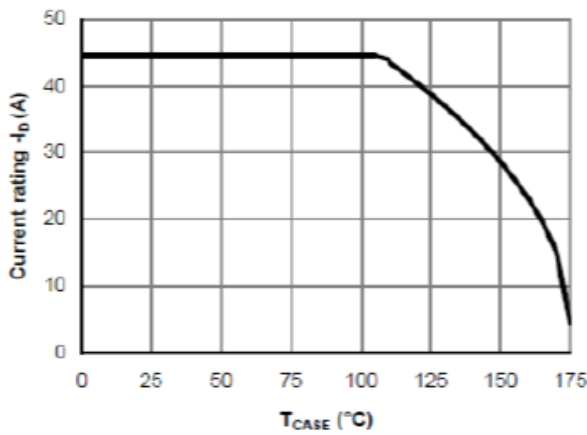


Figure 14: Current De-rating (Note B)

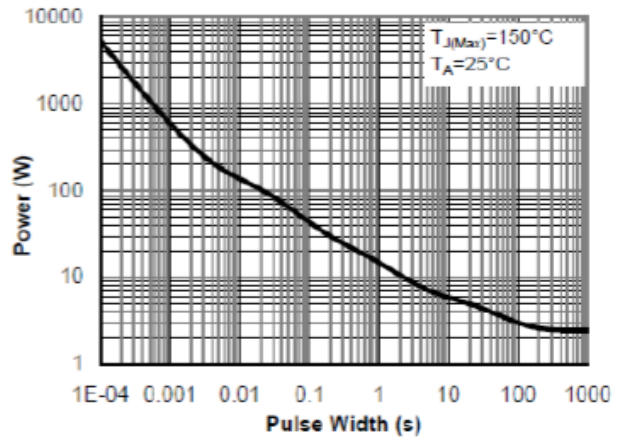


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note G)

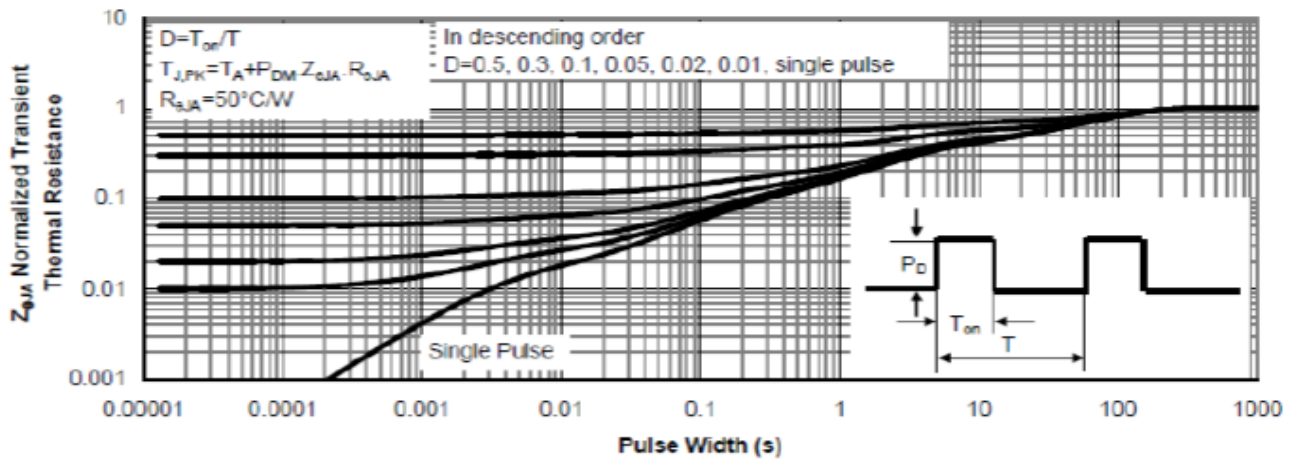


Figure 16: Normalized Maximum Transient Thermal Impedance (Note G)

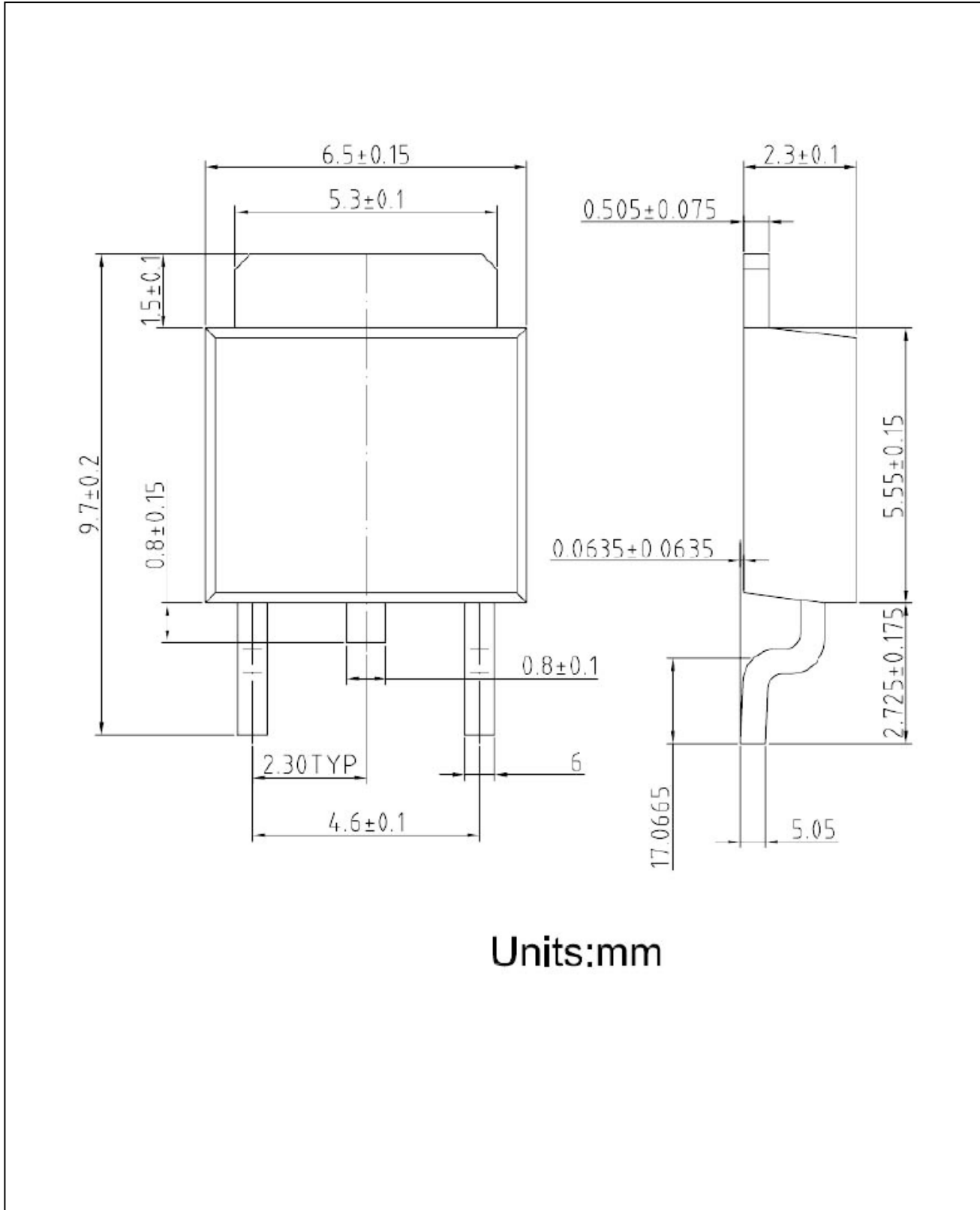


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Packing Information

TO-252



Units:mm



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Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.